

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	09/940885	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:23
L2	8746	(active near matrix near display)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:24
L3	312	(active near matrix near display) same ((active or semiconductor) adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:24
L4	1	(active near matrix near display) same ((active or semiconductor) adj layer) same (porous or void or pore)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:24
L5	72	(active near matrix near display) same ((active or semiconductor) adj layer) same (porous or void or pore or amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:24
L6	8	(active near matrix near display) same ((active or semiconductor) adj layer) same (porous or void or pore or amorphous) and helium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:25
L7	2	((active near matrix near display) same ((active or semiconductor) adj layer) same (porous or void or pore or amorphous)) and (((semiconductor or active) near layer) near10 helium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:26
L8	2	((active near matrix near display) same ((active or semiconductor) adj layer)) and (((semiconductor or active) near layer) near10 helium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:27
L9	2	((active near matrix near display) same ((active or semiconductor) adj layer)) and (((semiconductor or active) near layer) with helium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:27

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L10	27	((active near matrix near display) same ((active or semiconductor) adj layer)) and (((semiconductor or active) near layer) with (gas or helium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:29
L11	3283	((semiconductor or active) near layer) with (pore or porous or porosity or void)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:29
L12	543	((semiconductor or active) near layer) with (pore or porous or porosity or void).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:29
L13	484	((semiconductor or active) near layer) near10 (pore or porous or porosity or void).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:29
L14	31	((semiconductor or active) near layer) near10 (pore or porous or porosity or void).clm. and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:31
L15	26	((semiconductor or active) near layer) near5 (pore or porous or porosity or void).clm. and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:31
L16	11	((semiconductor or active) near layer) near5 (pore or porous or porosity or void) near10 (thick or thickness)) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:32
L17	20	((semiconductor or active) near layer) near5 (pore or porous or porosity or void) near10 (thick or thickness) near10 (nm or (nanometer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:33
L18	21	((semiconductor or active) near layer) near5 (pore or porous or porosity or void) near10 (deep or depth or thick or thickness) near10 (nm or (nanometer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:33
L19	30	((semiconductor or active) near layer) near10 (pore or porous or porosity or void) near10 (deep or depth or thick or thickness) near10 (nm or (nanometer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:34

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L20	1	((semiconductor or active) near layer) near10 (pore or porous or porosity or void) near10 (deep or depth or thick or thickness) near10 (nm or (nanometer))) and (active adj matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:35
L21	1	((semiconductor or active) near layer) near10 (pore or porous or porosity or void) near10 (nm or (nanometer))) and (active adj matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:35
L22	79	((semiconductor or active) near layer) near10 (pore or porous or porosity or void)) and (active adj matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:41
L23	30	((semiconductor or active) near layer) near10 (pore or porous or porosity or void) same gate same (insulating or dielectric or oxide or insulation)) and (active adj matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:36
L24	32580	((semiconductor or active) near layer) near10 (pore or porous or porosity or void) same gate same (insulating or dielectric or oxide or insulation) sam electrode) and (active adj matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:37
L25	26	((semiconductor or active) near layer) near10 (pore or porous or porosity or void) same gate same (insulating or dielectric or oxide or insulation) same electrode) and (active adj matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:37
L26	4	((semiconductor or active) near layer) near10 (pore or porous or porosity or void) same gate same (insulating or dielectric or oxide or insulation) same electrode same (tft or (thin adj film adj transistor))) and (active adj matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:38
L27	19	L22 and ((semiconductor or active) near5 surface near5 (pore or porous or void))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:41

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L28	17	I22 and (((semiconductor or active) near layer) near5 surface near5 (pore or porous or void))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:44
L29	11	I22 and (((semiconductor or active) near layer) near5 surface near5 (pore or porous or void)) and ((porous or pore or void) near5 (thickness or depth or thick or deep or deeper))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:48
L30	10	I22 and (((semiconductor or active) near layer) near5 surface near5 (pore or porous or void)) and ((porous or pore or void) near5 (thickness or depth or thick or deep or deeper)) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:48
L31	10	I22 and (((semiconductor or active) near layer) near5 surface near5 (pore or porous or void)) and ((porous or pore or void) near5 (thickness or depth or thick or deep or deeper)) and (tft or (thin adj film adj transistor)) and (active adj matrix)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:48

## EAST Search History

L46	33	I45 and 257/72	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 13:13
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